

20V N-Channel MOSFET



SOP-8



Pin Definition:

1. Source	8. Draii
2. Source	7. Draii
3. Source	6. Drai
1 0-4-	

Key Parameter Performance

Parameter	Value	Unit
V_{DS}	20	V
R _{DS(on)} (max)	30	m
Q _g	11.2	nC

Features

Advance Trench Process Technology High Density Cell Design for Ultra Low On-resistance

Application

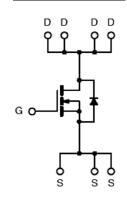
Specially Designed for Li-on Battery Packs Battery Switch Application

Ordering Information

Part No.	Package	Packing
TSM4424CS RL	SOP-8	2.5Kpcs / 13+Reel
TSM4424CS RLG	SOP-8	2.5Kpcs / 13+Reel
TSM4424CS RVG	SOP-8	3Kpcs / 13+Reel

Note: %⊕+denotes for Halogen- and Antimony-free as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds

Block Diagram



N-Channel MOSFET

Absolute Maximum Ratings (T_C = 25°C, unless otherwise noted)

Parameter		Symbol	Limit	Unit		
Drain-Source Voltage		V_{DS}	20	V		
Gate-Source Voltage		Gate-Source Voltage		V_{GS}	±8	V
Continuous Drain Current		I _D	8	А		
Pulsed Drain Current (Note 1)		I _{DM}	30	А		
Continuous Source Current (Diode Conduction)		Is	2.2	А		
Maximum Power Dissipation	Ta = 25°C		2.5	W		
	Ta = 75°C	P _D	1.3			
Operating Junction Temperature		T _J	+150	°C		
Operating Junction and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C		

Thermal Performance

Parameter	Symbol	Limit	Unit
Thermal Resistance Junction to Foot	R _{JF}	25	°C/W
Thermal Resistance Junction to Ambient	R _{JA}	52.5	°C/W



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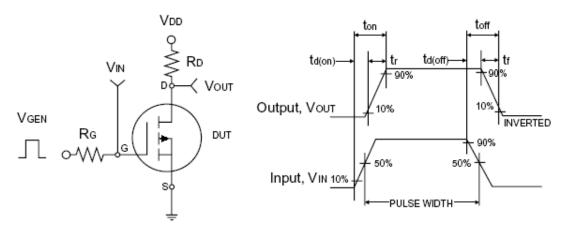


Electrical Specifications

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static ^(Note 2)						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250uA$	BV _{DSS}	20			V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250uA$	$V_{GS(TH)}$	-	0.65	1	V
Gate Body Leakage	$V_{GS} = \pm 8V, V_{DS} = 0V$	I _{GSS}	1		±100	nA
Zero Gate Voltage Drain Current	$V_{DS} = 20V, V_{GS} = 0V$	I _{DSS}	1		1.0	uA
On-State Drain Current	$V_{DS} = 5V, V_{GS} = 4.5V$	I _{D(ON)}	30			Α
	$V_{GS} = 4.5V, I_D = 4.5A$		-	23	30	
Drain-Source On-State Resistance	$V_{GS} = 2.5V, I_D = 3.5A$	R _{DS(ON)}	1	25	35	m
	$V_{GS} = 1.8V, I_D = 2.0A$		1	35	45	
Forward Transconductance	$V_{DS} = 10V, I_{D} = 6A$	g fs	1	40		S
Diode Forward Voltage	$I_S = 1.7A, V_{GS} = 0V$	V_{SD}	1	0.8	1.2	>
Dynamic ^(Note 3)						
Total Gate Charge	$V_{DS} = 10V, I_D = 4.5A,$	Q_g		11.2	14	
Gate-Source Charge		Q_gs		1.4		nC
Gate-Drain Charge	$V_{GS} = 4.5V$	Q_{gd}		2.2		
Input Capacitance	10)/)/	C _{iss}	-	500		
Output Capacitance	$V_{DS} = 10V, V_{GS} = 0V,$ f = 1.0MHz	C _{oss}	1	300		pF
Reverse Transfer Capacitance		C_{rss}	1	140		
Switching ^(Note 4)						
Turn-On Delay Time	$V_{DD} = 10V, R_{L} = 10 ,$ $I_{D} = 1A, V_{GEN} = 4.5V,$ $R_{G} = 6$	t _{d(on)}		15	25	
Turn-On Rise Time		t _r		30	60	20
Turn-Off Delay Time		t _{d(off)}		35	70	ns
Turn-Off Fall Time		t _f		15	45	

Notes:

- 1. Pulse width limited by the maximum junction temperature
- 2. Pulse test: PW m300µs, duty cycle m2%
- 3. For DESIGN AID ONLY, not subject to production testing.
- 4. Switching time is essentially independent of operating temperature.



Switching Test Circuit

Switchin Waveforms

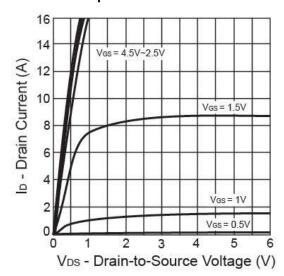


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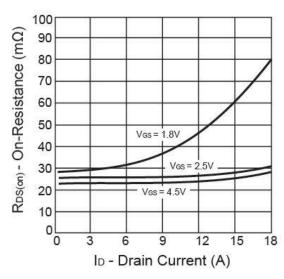
Pb ROHS COMPLIANT

Electrical Characteristics Curve

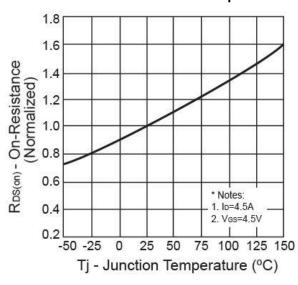
Output Characteristics



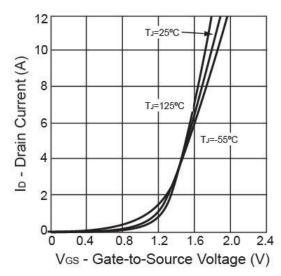
On-Resistance vs. Drain Current



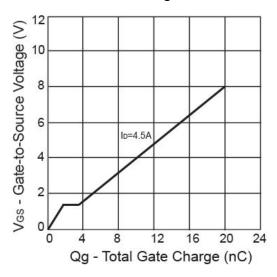
On-Resistance vs. Junction Temperature



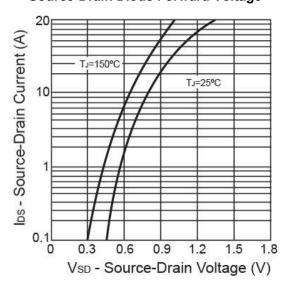
Transfer Characteristics



Gate Charge



Source-Drain Diode Forward Voltage



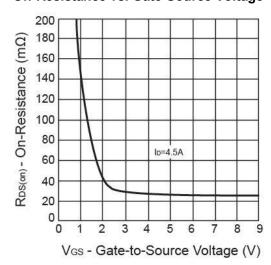


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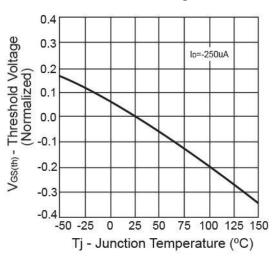


Electrical Characteristics Curve

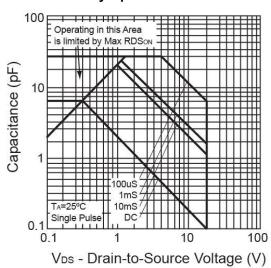
On-Resistance vs. Gate-Source Voltage



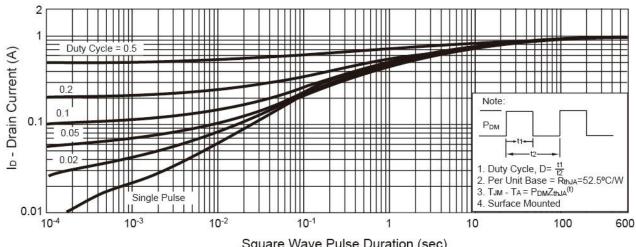
Threshold Voltage



Safety Operation Area



Normalized Thermal Transient Impedance, Junction-to-Ambient

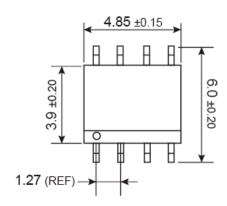


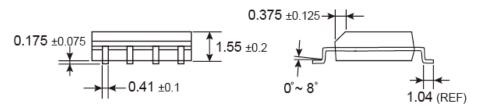
Square Wave Pulse Duration (sec)





SOP-8 Mechanical Drawing

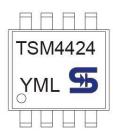




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Unit: Millimeters

Marking Diagram



Y = Year Code

M = Month Code

(**A**=Jan, **B**=Feb, **C**=Mar, **D**=Apl, **E**=May, **F**=Jun, **G**=Jul, **H**=Aug, **I**=Sep, **J**=Oct, **K**=Nov, **L**=Dec)

Month Code for Halogen Free Product
 (O=Jan, P=Feb, Q=Mar, R=Apl, S=May, T=Jun, U=Jul, V=Aug, W=Sep, X=Oct, Y=Nov, Z=Dec)

L = Lot Code

Version: C14



TSM4424 20V N-Channel MOSFET

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